

30V DUAL N AND P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

N-CHANNEL: $V_{(BR)DSS}=30V$; $R_{DS(ON)}=0.135\Omega$; $I_D=2.3A$

P-CHANNEL: $V_{(BR)DSS}=-30V$; $R_{DS(ON)}=0.185\Omega$; $I_D=-2.0A$

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



MSOP8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

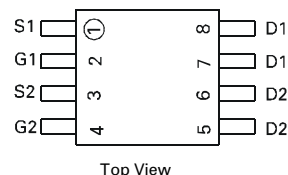
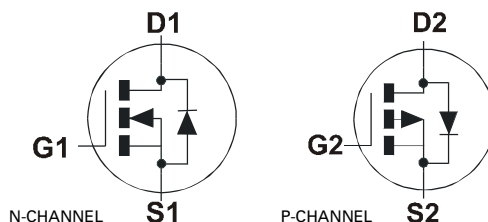
- DC - DC Converters
- Power Management Functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXMD63C03XTA	7	12mm embossed	1000 units
ZXMD63C03XTC	13	12mm embossed	4000 units

DEVICE MARKING

- ZXMD63C03



ZXMD63C03X

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-Source Voltage	V_{DSS}	30	-30	V
Gate- Source Voltage	V_{GS}	± 20		V
Continuous Drain Current ($V_{GS}=4.5V$; $T_A=25^\circ C$)(b)(d) ($V_{GS}=4.5V$; $T_A=70^\circ C$)(b)(d)	I_D	2.3 1.8	-2.0 -1.6	A
Pulsed Drain Current (c)(d)	I_{DM}	14	-9.6	A
Continuous Source Current (Body Diode)(b)(d)	I_S	1.5	-1.4	A
Pulsed Source Current (Body Diode)(c)(d)	I_{SM}	14	-9.6	A
Power Dissipation at $T_A=25^\circ C$ (a)(d) Linear Derating Factor	P_D	0.87 6.9		W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (a)(e) Linear Derating Factor	P_D	1.04 8.3		W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b)(d) Linear Derating Factor	P_D	1.25 10		W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150		$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	143	$^\circ C/W$
Junction to Ambient (b)(d)	$R_{\theta JA}$	100	$^\circ C/W$
Junction to Ambient (a)(e)	$R_{\theta JA}$	120	$^\circ C/W$

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

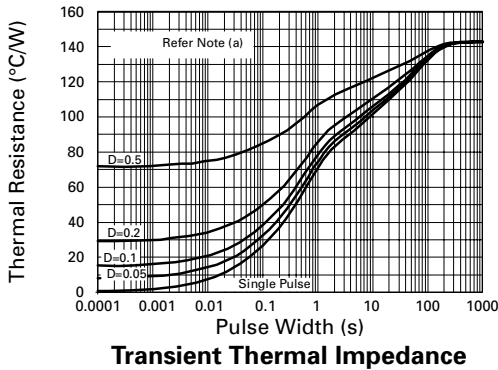
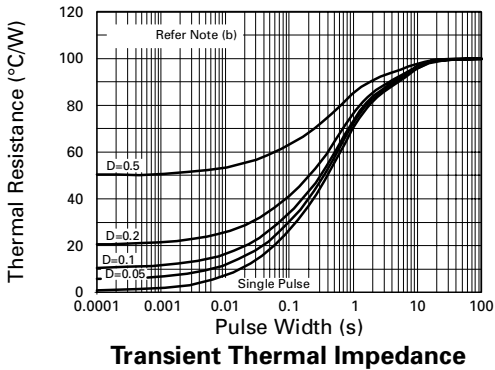
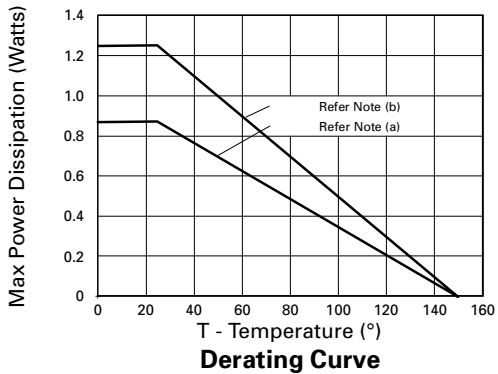
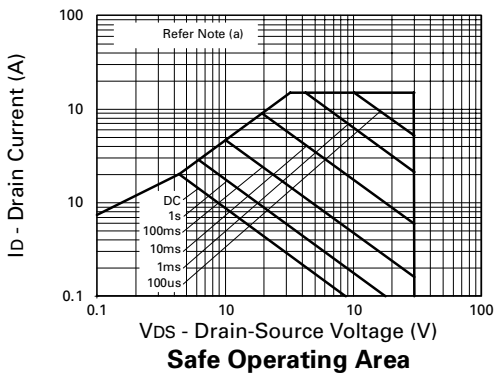
(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

(d) For device with one active die.

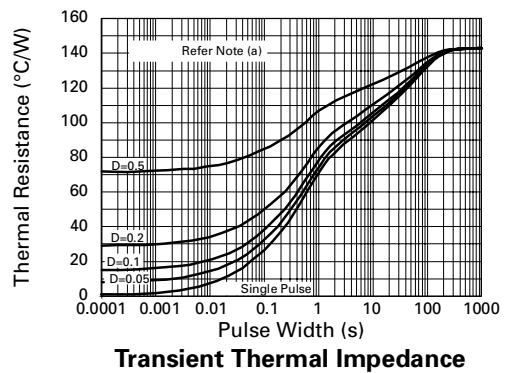
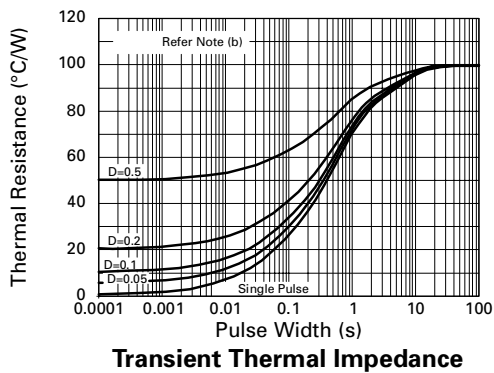
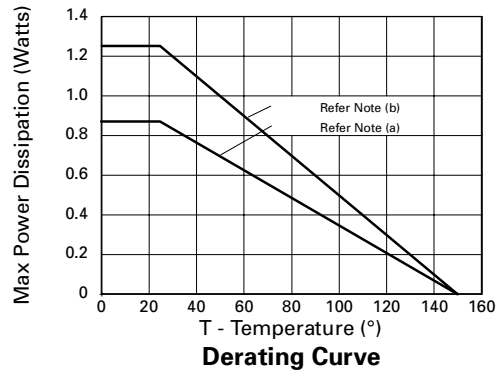
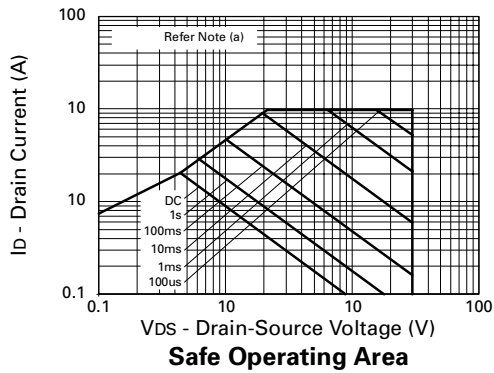
(e) For device with two active die running at equal power.

N-CHANNEL CHARACTERISTICS



ZXMD63C03X

P-CHANNEL CHARACTERISTICS



N-CHANNEL

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

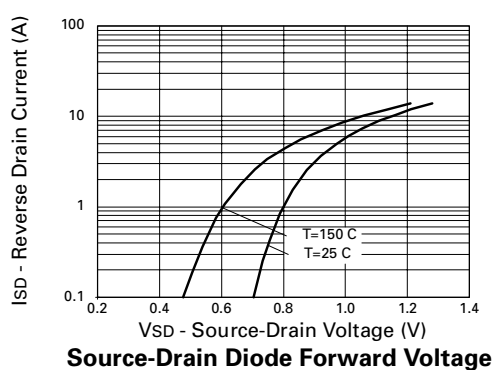
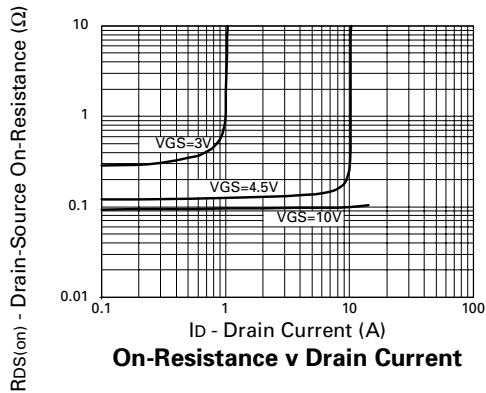
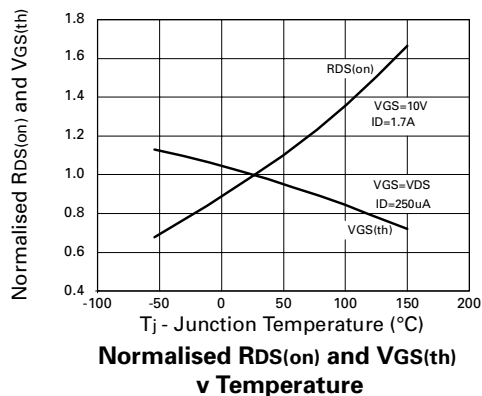
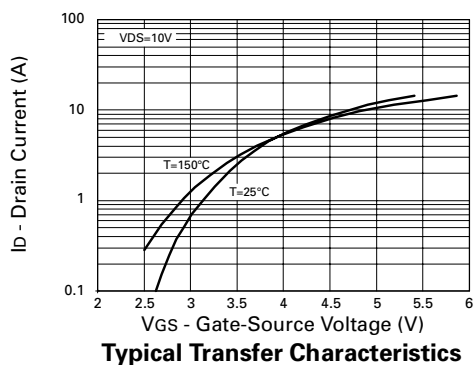
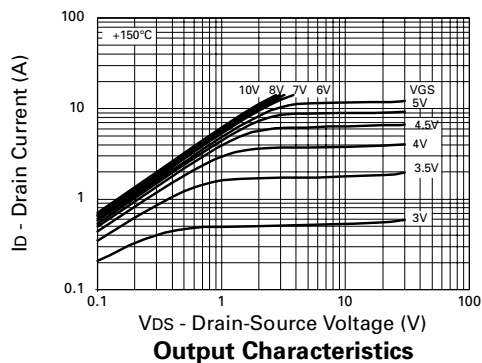
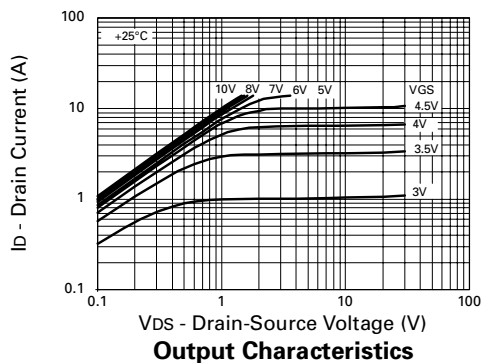
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	30			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =± 20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	1.0			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.135 0.200	Ω Ω	V _{GS} =10V, I _D =1.7A V _{GS} =4.5V, I _D =0.85A
Forward Transconductance (3)	g _{fs}	1.9			S	V _{DS} =10V, I _D =0.85A
DYNAMIC (3)						
Input Capacitance	C _{iss}		290		pF	V _{DS} =25 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		70		pF	
Reverse Transfer Capacitance	C _{rss}		20		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		2.5		ns	V _{DD} =15V, I _D =1.7A R _G =6.1Ω, R _D =8.7Ω (Refer to test circuit)
Rise Time	t _r		4.1		ns	
Turn-Off Delay Time	t _{d(off)}		9.6		ns	
Fall Time	t _f		4.4		ns	
Total Gate Charge	Q _g			8	nC	V _{DS} =24V, V _{GS} =10V, I _D =1.7A (Refer to test circuit)
Gate-Source Charge	Q _{gs}			1.2	nC	
Gate Drain Charge	Q _{gd}			2	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			0.95	V	T _j =25°C, I _S =1.7A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		16.9		ns	T _j =25°C, I _F =1.7A, di/dt= 100A/μs
Reverse Recovery Charge(3)	Q _{rr}		9.5		nC	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.

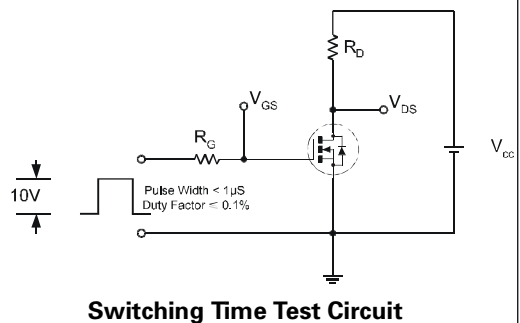
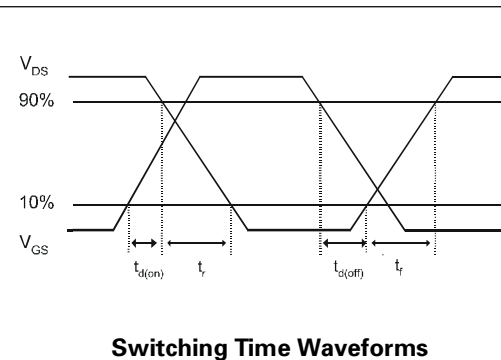
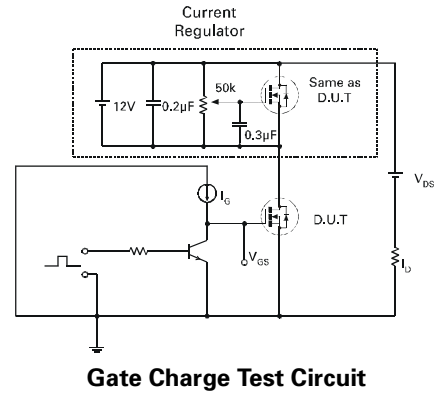
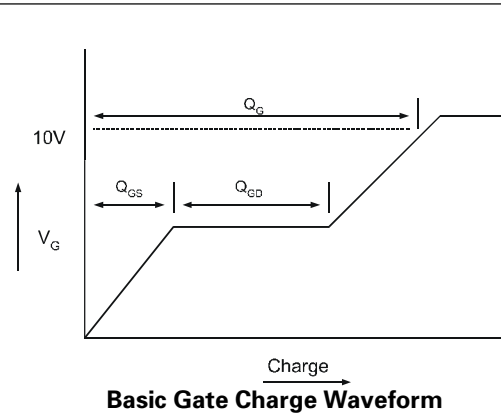
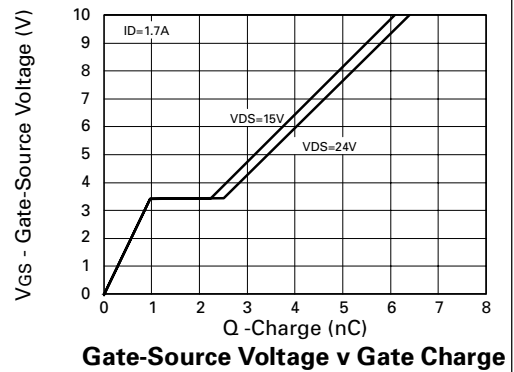
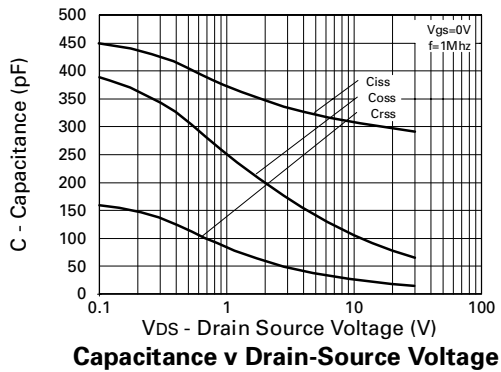
(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

N-CHANNEL TYPICAL CHARACTERISTICS



N-CHANNEL CHARACTERISTICS



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P-CHANNEL

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

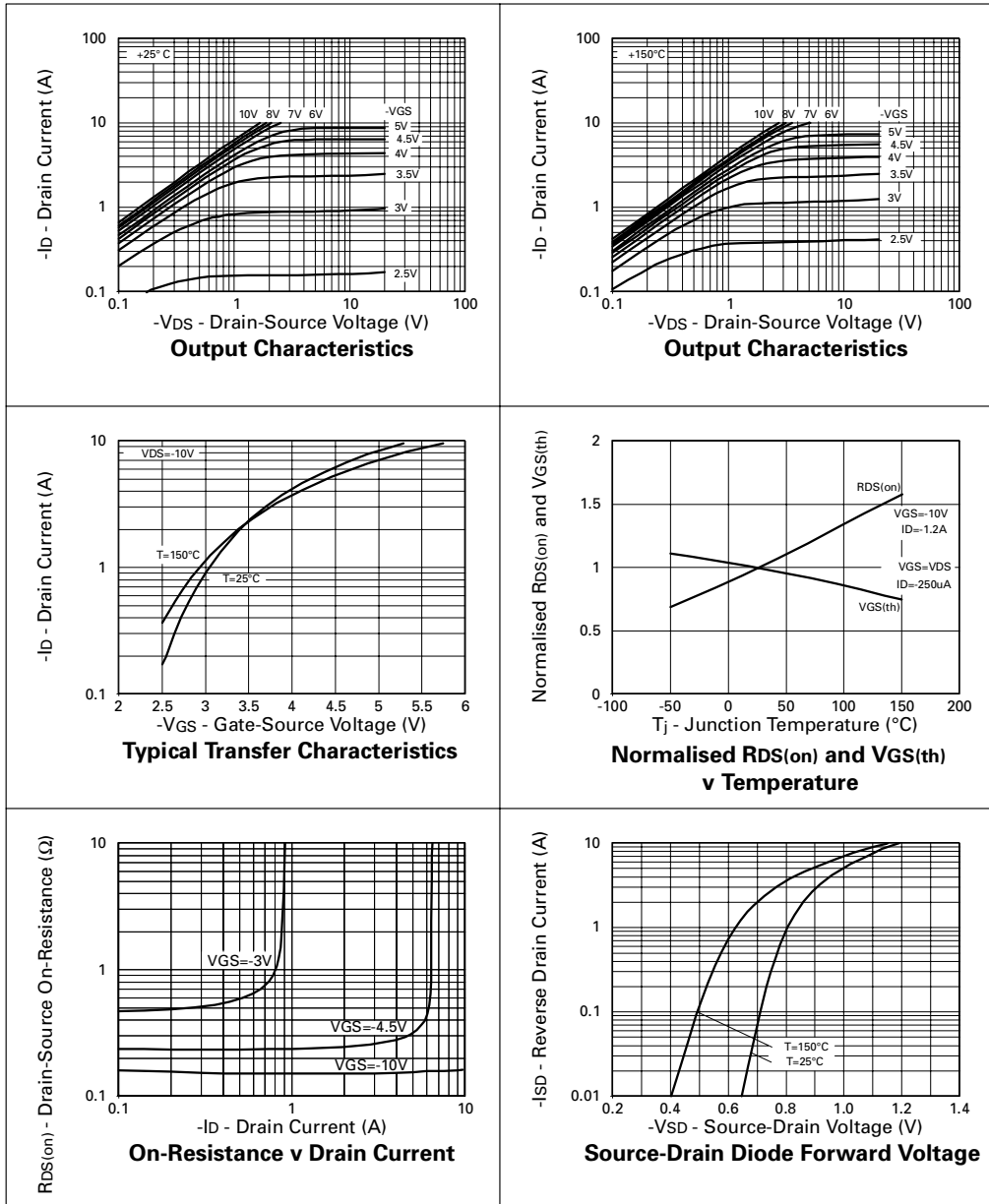
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	V _{DS} =-30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			±100	nA	V _{GS} =± 20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	I _D =-250μA, V _{DS} =V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.185 0.27	Ω Ω	V _{GS} =-10V, I _D =-1.2A V _{GS} =-4.5V, I _D =-0.6A
Forward Transconductance (3)	g _{fs}	0.92			S	V _{DS} =-10V,I _D =-0.6A
DYNAMIC (3)						
Input Capacitance	C _{iss}		270		pF	V _{DS} =-25 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		80		pF	
Reverse Transfer Capacitance	C _{rss}		30		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		2.6		ns	V _{DD} =-15V, I _D =-2.4A R _G =6.2Ω, R _D =6.2Ω (Refer to test circuit)
Rise Time	t _r		4.8		ns	
Turn-Off Delay Time	t _{d(off)}		13.1		ns	
Fall Time	t _f		9.3		ns	
Total Gate Charge	Q _g			7	nC	V _{DS} =-24V,V _{GS} =-10V, I _D =-1.2A (Refer to test circuit)
Gate-Source Charge	Q _{gs}			1.2	nC	
Gate Drain Charge	Q _{gd}			2	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			-0.95	V	T _J =25°C, I _S =-1.2A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		21.4		ns	T _J =25°C, I _F =-1.2A, di/dt= 100A/μs
Reverse Recovery Charge(3)	Q _{rr}		15.7		nC	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.

(2) Switching characteristics are independent of operating junction temperature.

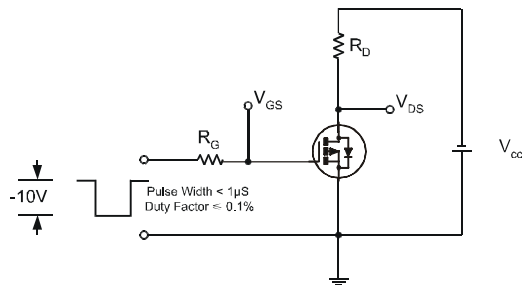
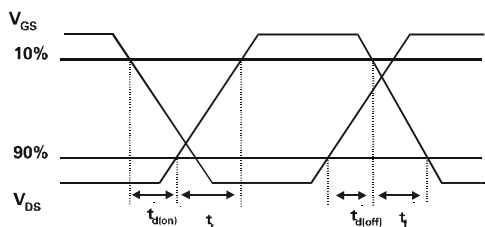
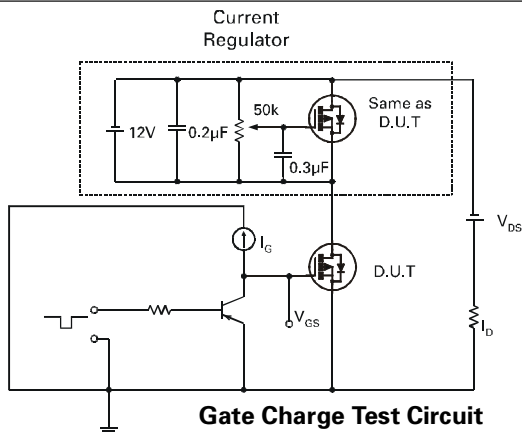
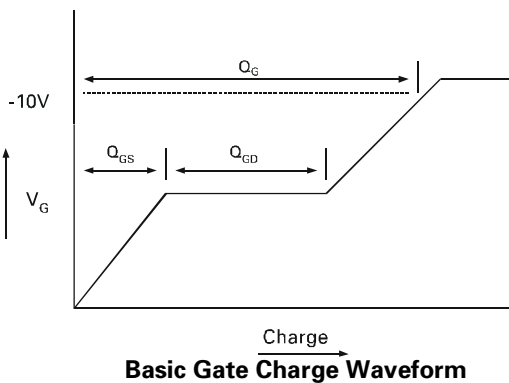
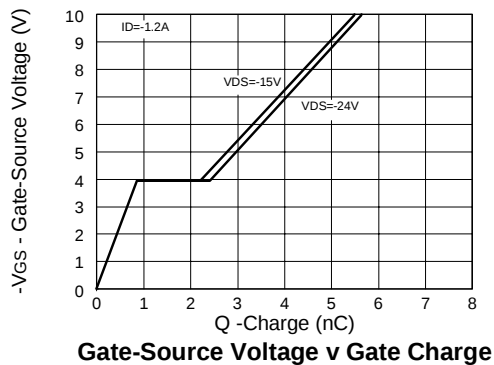
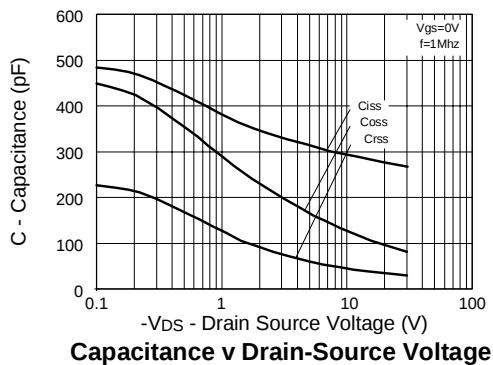
(3) For design aid only, not subject to production testing.

P-CHANNEL CHARACTERISTICS



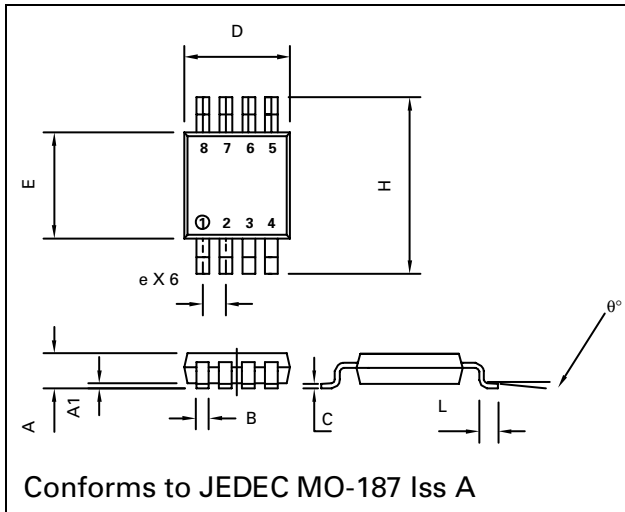
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P-CHANNEL TYPICAL CHARACTERISTICS



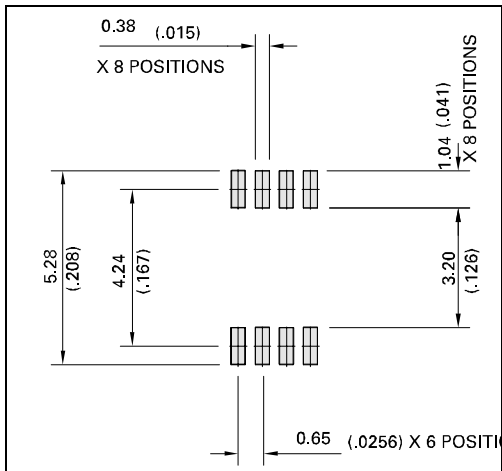
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PACKAGE DIMENSIONS



DIM	Millimetres		Inches	
	MIN	MAX	MIN	MAX
A		1.10		0.043
A1	0.05	0.15	0.002	0.006
B	0.25	0.40	0.010	0.016
C	0.13	0.23	0.005	0.009
D	2.90	3.10	0.114	0.122
e	0.65	BSC	0.0256	BSC
E	2.90	3.10	0.114	0.122
H	4.90	BSC	0.193	BSC
L	0.40	0.70	0.016	0.028
q°	0°	6°	0°	6°

PAD LAYOUT DETAILS



ZETEX

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